

# SUNDAY, March 26, TUTORIALS 8 a.m.-5:00 p.m.

<p style="text-align: center;">101. Reliability definitions and basic concepts R. Degraeve (IMEC) (8:00-11:30 a.m.)</p>	<p style="text-align: center;">121. SER fundamentals N. Seifert (Intel) (8:00-9:30 a.m.)</p>	<p style="text-align: center;">151. Analog and digital circuits K. Roy (Purdue) (8:00-9:30 a.m.)</p>	<p style="text-align: center;">170. FeRam reliability J. Rodriguez (TI) (8:00-9:30 a.m.)</p>
	<p style="text-align: center;">122. Soft error detection and mitigation in computer system C. Slayman (Sun Micro) (10:00-11:30 a.m.)</p>	<p style="text-align: center;">152. Mixed signal circuit reliability from device stress conditions to IC-failure C. Schluender (Infineon) (10:00-11:30 a.m.)</p>	<p style="text-align: center;">180. Hydrogen in Si S. Ashok (Penn State) (10:00-11:30 a.m.)</p>
<p style="text-align: center;">102. Fast wafer level reliability monitoring fWLR A. Martin (Infineon) (1:30-3:00 p.m.)</p>	<p style="text-align: center;">130. Advanced interconnect processes for the 45nm node and beyond J. Gambino (IBM) (1:30-3:00 p.m.)</p>	<p style="text-align: center;">160. ESD and latchup G. Boselli (TI) (1:30-3:00 p.m.)</p>	<p style="text-align: center;">191. NBTI: A simple view of a complex phenomena A. Alam (Purdue) (1:30-3:00 p.m.)</p>
<p style="text-align: center;">110. Process induced damage – a history and prognosis T. Hook (IBM) 3:30-5:00 p.m.</p>	<p style="text-align: center;">140. Physics of silicon package interactions with special regard to reliability K. Seshan (Intel) 3:30-5:00 p.m.</p>		<p style="text-align: center;">192. Electrical characterization and modeling of NBTI in p-MOSFET devices S. Mahapatra (IIT Bombay) 3:30-5:00 p.m.</p>